

# Oves Badami

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/11252045/publications.pdf>

Version: 2024-02-01

15  
papers

118  
citations

1478505

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h-index

1474206

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g-index

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15  
docs citations

15  
times ranked

99  
citing authors

#	ARTICLE	IF	CITATIONS
1	Simulation of the Impact of Ionized Impurity Scattering on the Total Mobility in Si Nanowire Transistors. <i>Materials</i> , 2019, 12, 124.	2.9	21
2	An Improved Surface Roughness Scattering Model for Bulk, Thin-Body, and Quantum-Well MOSFETs. <i>IEEE Transactions on Electron Devices</i> , 2016, 63, 2306-2312.	3.0	20
3	Nano-electronic Simulation Software (NESS): a flexible nano-device simulation platform. <i>Journal of Computational Electronics</i> , 2020, 19, 1031-1046.	2.5	20
4	Mobility of Circular and Elliptical Si Nanowire Transistors Using a Multi-Subband 1D Formalism. <i>IEEE Electron Device Letters</i> , 2019, 40, 1571-1574.	3.9	15
5	Comprehensive Study of Cross-Section Dependent Effective Masses for Silicon Based Gate-All-Around Transistors. <i>Applied Sciences (Switzerland)</i> , 2019, 9, 1895.	2.5	15
6	Variability Predictions for the Next Technology Generations of n-type SixGe1 $\hat{a}$ ~x Nanowire MOSFETs. <i>Micromachines</i> , 2018, 9, 643.	2.9	7
7	A Kinetic Monte Carlo Study of Retention Time in a POM Molecule-Based Flash Memory. <i>IEEE Nanotechnology Magazine</i> , 2020, 19, 704-710.	2.0	5
8	Enhanced Capabilities of the Nano-Electronic Simulation Software (NESS). , 2020, , .		5
9	Surface Roughness Scattering in NEGF using self-energy formulation. , 2019, , .		3
10	Multiscale Modeling of Charge Trapping in Molecule Based Flash Memories. , 2019, , .		2
11	SchrÅ¶dinger Equation Based Quantum Corrections in Drift-Diffusion: A Multiscale Approach. , 2019, , .		2
12	Physical Insights into the Transport Properties of RRAMs Based on Transition Metal Oxides. , 2019, , .		1
13	KMC-based POM flash cell optimization and time-dependent performance investigation. <i>Semiconductor Science and Technology</i> , 2021, 36, 075021.	2.0	1
14	Study of gate current in advanced MOS architectures. <i>Solid-State Electronics</i> , 2022, 194, 108345.	1.4	1
15	Advanced Simulation of RRAM Memory Cells. , 2019, , .		0